## HMCTM PIN Diode SP2T 20 Watt Suitch for 0.05-6.0 GHz Higher Power Applications

## Features

- Exceptional Broadband Performance, 0.05-6.0 GHz
- Low Loss: Tx = 0.24 dB Avg @ $2025 \mathrm{MHz}, 35 \mathrm{~mA}$
- $\mathrm{Tx}=0.38 \mathrm{~dB}$ Avg @ $3500 \mathrm{MHz}, 35 \mathrm{~mA}$
- High Isolation: Rx=31.0 dB Avg @ 2025 MHz
- $\quad \mathrm{Rx}=27 \mathrm{~dB}$ Avg @ 3500 MHz
- High RF C.W. Input Power: 20 W C.W. (Tx-Ant Port)
- Higher IIP3: > 64 dBm (Tx-Ant Port )
- Suitable for High Power TD-SCDMA \& WiMAX Applications
- Surface Mount 3mm PQFN Package
- RoHS* Compliant and $260^{\circ} \mathrm{C}$ Re-flow Compatible


## Description and Applications

The MASW-000825-12770T is a compact SP2T PIN diode switch in a lead-free 3mm MLP plastic package that offers extraordinary performance with excellent isolation to loss ratio for both $\mathrm{T}_{\mathrm{x}}$ and $\mathrm{R}_{\mathrm{x}}$ states. The SP2T provides outstanding 20 W C.W. power handling coupled with 64 dBm IIP3 for maximum switch performance.

The MASW-000825-12770T is a $0.05-6.0 \mathrm{GHz}$ SP2T High Peak and Average Power PIN diode switch used for T/R or LNA Protect Switch applications such as WiMAX and TDSCDMA.

This device incorporates a PIN diode die fabricated with M/A-COM Technology Solutions patented Silicon-Glass HMIC ${ }^{\text {TM }}$ process. This chip features two silicon pedestals embedded in a low loss, low dispersion glass. The diodes are formed on the top of each pedestal. The topside is fully encapsulated with silicon nitride and has an additional polymer passivation layer. These polymer protective coatings prevent damage and contamination during handling and assembly.

## Ordering Information

| Part Number | Package |
| :---: | :---: |
| MASW-000825-12770T | 1000 piece reel |
| MASW-000825-001SMB | Sample Board |
| MADR-008888-0002TB | Sample Board with recommended <br> external Driver \& MASW-000825- <br> 12770T Switch |

Functional Diagram (TOP VIEW)


Circuit Side View


Pin Configuration:
(Center Metal Area is RF, D.C., and Thermal Ground)

| PIN | Function | PIN | Function |
| :---: | :---: | :---: | :---: |
| 1 | N/C | 9 | GND |
| 2 | GND | 10 | Rx |
| 3 | $\mathrm{~T}_{\mathrm{x}}$ | 11 | GND |
| 4 | GND | 12 | N/C |
| 5 | N/C | 13 | GND |
| 6 | N/C | 14 | Ant |
| 7 | N/C | 15 | GND |
| 8 | N/C | 16 | N/C |

* Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.


## HMCTM PIN Diode SP2T 20 Watt Suitch for <br> 0.05-6.0 GHz Higher Power Applications

Electrical Specifications at $+25^{\circ} \mathrm{C}$, Characteristic Impedance $Z_{0}=50 \Omega, 35 \mathrm{~mA} / 28 \mathrm{~V}$

| Parameter | Symbol | 35mA / 28V Conditions | Units | Min. | Typ. | Max. |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| F = 2.0-2.7 GHz |  |  |  |  |  |  |
| Insertion Loss, Rx | Rx, IL | Bias: See Table Below, Pinc=0 dBm | dB |  | 0.42 | 0.55 |
| Insertion Loss, Tx | Tx, IL | Bias: See Table Below, Pinc=0 dBm | dB |  | 0.29 | 0.38 |
| Isolation, Tx To Rx | Rx, ISO | Bias: See Table Below, Pinc=0 dBm | dB | 24.5 | 28.6 |  |
| Isolation, Rx To Tx | Tx, ISO | Bias: See Table Below, Pinc=0 dBm | dB | 21.3 | 24.2 |  |
| Tx Input Return Loss | Tx, RL | Bias: See Table Below, Pinc=0 dBm | dB |  | -28 |  |
| Rx Input Return Loss | Rx, RL | Bias: See Table Below, Pinc=0 dBm | dB |  | -28 |  |
| $\mathrm{F}=3.3$-3.8 GHz |  |  |  |  |  |  |
| Insertion Loss, Rx | Rx, IL | Bias: See Table Below, Pinc=0 dBm | dB |  | 0.56 | 0.71 |
| Insertion Loss, Tx | Tx, IL | Bias: See Table Below, Pinc=0 dBm | dB |  | 0.38 | 0.48 |
| Isolation, Tx To Rx | Rx, ISO | Bias: See Table Below, Pinc= 0 dBm | dB | 22 | 26 |  |
| Isolation, Rx To Tx | Tx, ISO | Bias: See Table Below, Pinc=0 dBm | dB | 19.7 | 21.6 |  |
| Tx Input Return Loss | Tx, RL | Bias: See Table Below, Pinc=0 dBm | dB |  | -28 |  |
| Rx Input Return Loss | Rx, RL | Bias: See Table Below, Pinc=0 dBm | dB |  | -28 |  |
| $\mathrm{F}=4.9-5.9 \mathrm{GHz}$ |  |  |  |  |  |  |
| Insertion Loss, Rx | Rx, IL | Bias: See Table Below, Pinc= 0 dBm | dB |  | 0.95 | 1.10 |
| Insertion Loss, Tx | Tx, IL | Bias: See Table Below, Pinc=0 dBm | dB |  | 0.59 | 0.71 |
| Isolation, Tx To Rx | Rx, ISO | Bias: See Table Below, Pinc=0 dBm | dB | 19.5 | 22.4 |  |
| Isolation, Rx To Tx | Tx, ISO | Bias: See Table Below, Pinc=0 dBm | dB | 16.5 | 18.5 |  |
| Tx Input Return Loss | Tx, RL | Bias: See Table Below, Pinc=0 dBm | dB |  | -25 |  |
| Rx Input Return Loss | Rx, RL | Bias: See Table Below, Pinc=0 dBm | dB |  | -24 |  |


| Port | Tx | Rx | ANT |
| :--- | :--- | :--- | :--- |
| Pin | Pin 3 | Pin 10 | Pin 14 |
| Tx-ANT Isolation | $+28 \mathrm{~V} @ 0 \mathrm{ma}$ | 0 V | $+5 \mathrm{~V} @ 35 \mathrm{~mA}$ |
| Tx-ANT Insertion Loss | 0 V | $+28 \mathrm{~V} @ 0 \mathrm{ma}$ | $+5 \mathrm{~V} @ 35 \mathrm{~mA}$ |
| Rx-ANT Isolation | 0 V | $+28 \mathrm{~V} @ 0 \mathrm{ma}$ | $+5 \mathrm{~V} @ 35 \mathrm{~mA}$ |
| Rx-ANT Insertion Loss | +28V @ 0 ma | 0 V | $+5 \mathrm{~V} @ 35 \mathrm{~mA}$ |

## HMCTM PIN Diode SP2T 20 Watt Suitch for <br> 0.05-6.0 GHz Higher Power Applications

Electrical Specifications at $+\mathbf{2 5}^{\circ} \mathrm{C}$, Characteristic Impedance, $\mathrm{Z}_{\mathbf{0}}=50 \Omega$

| Parameter | Symbol | Conditions | Units | Min | Typ | Max |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Tx $2^{\text {nd }}$ Harmonic | $\begin{gathered} \text { Tx } \\ \text { 2Fo } \end{gathered}$ | $\begin{gathered} \text { Fo }=2.010 \mathrm{GHz}, \mathrm{Tx}=+5.0 \mathrm{~V} @+35 \mathrm{~mA}, \\ \mathrm{Rx}=+28 \mathrm{~V} @ 0 \mathrm{~mA} \\ \text { Pin }=+30 \mathrm{dBm}, \text { Tx To Antenna } \end{gathered}$ | dBc |  | 70 |  |
| Tx $3^{\text {rd }}$ Harmonic | $\begin{gathered} \text { Tx } \\ \text { 3Fo } \end{gathered}$ | $\begin{gathered} \text { Fo }=2.010 \mathrm{GHz}, \mathrm{Tx}=+5.0 \mathrm{~V} @+35 \mathrm{~mA}, \\ \mathrm{Rx}=+28 \mathrm{~V} @ 0 \mathrm{~mA} \\ \text { Pin }=+30 \mathrm{dBm} \text {, Tx To Antenna } \end{gathered}$ | dBc |  | 86 |  |
| Tx Input Third Order Intercept Point | $\begin{gathered} \text { Tx } \\ \text { IIP3 } \end{gathered}$ | $\begin{gathered} \mathrm{Tx}=+5.0 \mathrm{~V} @+35 \mathrm{~mA}, \mathrm{Rx}=+28 \mathrm{~V} @ 0 \mathrm{~mA} \\ \mathrm{Pi}=+20 \mathrm{dBm}, \\ \mathrm{~F} 1=2.010 \mathrm{GHz}, \mathrm{~F} 2=2.020 \mathrm{GHz}, \\ \text { Tx To Antenna } \end{gathered}$ | dBm |  | 64 |  |
| Tx C.W. Input Power ${ }^{2}$ | Tx CW Pinc | $\begin{gathered} \mathrm{Tx}=+5.0 \mathrm{~V} @+35 \mathrm{~mA}, \\ \mathrm{Rx}=+28 \mathrm{~V} @ 0 \mathrm{~mA} \\ \mathrm{~F}=2.010,3.500 \mathrm{GHz}, \mathrm{Tx} \text { To Antenna } \end{gathered}$ | dBm <br> W |  |  | $\begin{aligned} & 43 \\ & 20 \end{aligned}$ |
| Tx Peak Input Power | Tx Pk Pinc | $\begin{gathered} \mathrm{Tx}=+5.0 \mathrm{~V} @+35 \mathrm{~mA}, \\ \mathrm{Rx}=+28 \mathrm{~V} @ 0 \mathrm{~mA} \end{gathered}$ <br> $\mathrm{F}=2.010 \mathrm{GHz}, \mathrm{Tx}$ To Antenna ( $5 \mu$ S RF Pulse Width, 1\% Duty 1.10:1 Ant VSWR ) | dBm W |  |  | $\begin{gathered} 53 \\ 200 \end{gathered}$ |
| Rx C.W. Input Power | Rx CW Pinc | $\begin{gathered} \mathrm{Rx}=+5.0 \mathrm{~V} @+35 \mathrm{~mA}, \mathrm{Tx}=+28 \mathrm{~V} @ 0 \mathrm{~mA} \\ \mathrm{~F}=2.010 \mathrm{GHz} \text {, Antenna to Rx } \end{gathered}$ | $\begin{gathered} \mathrm{dBm} \\ \mathrm{~W} \end{gathered}$ |  |  | $\begin{gathered} 39 \\ 8 \end{gathered}$ |
| Tx Input P1dB | $\begin{gathered} \text { Tx } \\ \text { P1dB } \end{gathered}$ | $\begin{gathered} \mathrm{Tx}=+5.0 \mathrm{~V} @+35 \mathrm{~mA}, \\ \mathrm{Rx}=+28 \mathrm{~V} @ \text { OmA } \\ \mathrm{F}=2.010, \mathrm{GHz}, \mathrm{Tx} \text { To Antenna } \end{gathered}$ | dBm |  | >43 |  |
| Tx RF Switching Speed | $\tau_{\text {RF }}$ | $\begin{gathered} (10 \%-90 \% \text { RF Voltage }) \\ \mathrm{Tx}=+5.0 \mathrm{~V} @+35 \mathrm{~mA}, \mathrm{Rx}=+28 \mathrm{~V} @ \text { 0mA } \\ \mathrm{F}=2.010 \mathrm{GHz}, \mathrm{Tx} \text { To Antenna } \\ 1 \mathrm{MHz} \text { Rep Rate in Modulating Mode } \end{gathered}$ | ns |  | 200 |  |

Absolute Maximum Ratings ${ }^{1}$
@ $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ (unless otherwise specified)

| Parameter | Absolute Maximum |
| :---: | :---: |
| Forward Current | 100 mA |
| Reverse Voltage (RF \& D.C. ) | -140 V |
| Operating Temperature | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |
| Storage Temperature | $-55^{\circ} \mathrm{C}$ to $+150{ }^{\circ} \mathrm{C}$ |
| Junction Temperature | $+175^{\circ} \mathrm{C}$ |
| Tx Incident C.W. Power |  |

[^0]
## Handling Procedures

Please observe the following precautions to avoid damage:

## Static Sensitivity

These devices are rated Class 1B Human Body. Proper ESD control techniques should be used when handling these devices.

## HMCTM PIN Diode SP2T 20 Watt SMitch for <br> 0.05-6.0 GHz Higher Power Applications

## D.C. Bias to RF Truth Table

| RF State | TTL \& D.C. Bias Conditions | Voltage at Common Anode |
| :---: | :---: | :---: |
|  <br> Isolation Tx-Rx | $+5 \mathrm{~V} @ 35 \mathrm{~mA}(\mathrm{Tx}),+28 \mathrm{~V} @ 0 \mathrm{~mA}(\mathrm{Rx})$ | +0.9 V |
|  <br> Isolation Rx-Tx | $+5 \mathrm{~V} @ 35 \mathrm{~mA}(\mathrm{Rx}),+28 \mathrm{~V} @ 0 \mathrm{~mA}(\mathrm{Tx})$ | +0.9 V |

## Driver and SP2T Schematic with Positive Voltage



## Notes:

1. Data is taken on M/A-COM evaluation board 1000029181-0000001@25C by removing peripheral board losses (connectors, transmission line, and bias elements ).
2. Typical PIN Diode Forward Voltage $=+0.9 \mathrm{~V} @+35 \mathrm{~mA}$ for Insertion Loss. Typical PIN Diode Reverse Voltage = 28 V - $1.0 \mathrm{~V}=27 \mathrm{~V}$ for Isolation.
3. Switch is Asymmetrical, +43 dBm RF C.W. Input Power Applies to Tx Port Only.
4. Center Ground Area of MLP 3mm Package must be Attached to Thermal Ground for Optimum RF Power Performance.
5. M/A-Com Recommends the usage of the MADR-008888-000100 driver with this switch.

## Assembly Note:

A typical soldering process profile and handling instructions are provided in Application Notes, S2083 "Surface Mount Instructions for QFN / DFN Packages" on the M/A-Com website at www.macomtech.com

Typical Small Signal Performance at $\mathbf{+ 2 5 ^ { \circ }} \mathbf{C}$, Characteristic Impedance, $Z_{0}=50 \Omega$


Bias:+28V @ 0mA


# Typical Small Signal Performance over Temperature Characteristic Impedance, $\mathrm{Z}_{0}=50 \Omega$ 



Typical Small Signal Performance over temperature Characteristic Impedance, $Z_{0}=50 \Omega$


## HMCTM PIN Diode SP2T 20 Watt Svitch for <br> 0.05-6.0 GHz Higher Power Applications

MASW-000825-12770T Outline ${ }^{\dagger}$ - Lead Free 3mm PQFP-N 16 Lead Saw Singulated


[^1]Meets JEDEC moisture sensitivity level 1 requirements.

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[^0]:    1. Exceeding these limits may cause permanent damage.
    2. Refer to page 7 of the datasheet for power handling curves.
[^1]:    $\dagger$ Reference Application Note S2083 for lead-free solder reflow recommendations.

